



The contribution of exciton-phonon interaction and action disorder to near-band-edge extrinsic absorption in II-III₂-VI₄ compounds

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Abstract

Results of a study of near-band-edge absorption in both initial and annealed CdGa₂S₄ and CdIn₂S₄ single crystals at different temperatures are presented. Exciton-phonon interaction and cation disorder are shown to determine the absorption edge in CdGa₂S₄ and CdIn₂S₄ sompounds correspondingly.